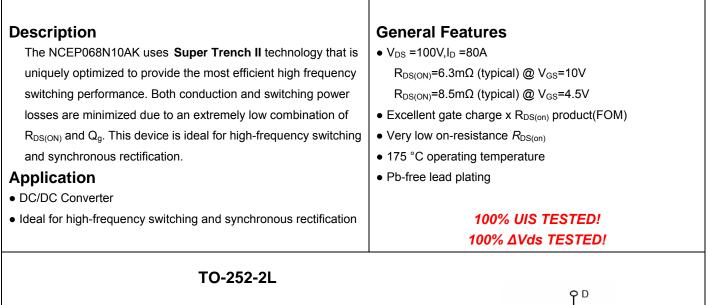
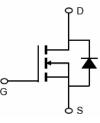


NCE N-Channel Super Trench II Power MOSFET







Schematic Diagram

Package Marking and Ordering Information

U	0	J			
Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP068N10AK	NCEP068N10AK	TO-252-2L	-	-	-

Absolute Maximum Ratings (T_c=25[°]C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	VDS	100	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	Ι _D	80	А
Drain Current-Continuous(T _C =100℃)	I _D (100℃)	61	А
Pulsed Drain Current	I _{DM}	320	A
Maximum Power Dissipation	PD	125	W
Derating factor		0.83	₩ /°C
Single pulse avalanche energy (Note 5)	E _{AS}	320	mJ
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 175	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	R _{θJC}	1.2	°C/W	
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Electrical Characteristics (T_c=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	· · ·					
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	100		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V_{GS} =±20V, V_{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)	· · ·					
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	1.2	1.8	2.4	V
Drain-Source On-State Resistance	Р	V_{GS} =10V, I _D =40A	-	6.3	6.8	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V_{GS} =4.5V, I _D =40A	-	8.5	9.8	mΩ
Gate resistance	Rg	F=1.0MHz		1.3		Ω
Forward Transconductance	g fs	V _{DS} =5V,I _D =40A		60	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}		-	4680	-	PF
Output Capacitance	C _{oss}	V _{DS} =50V,V _{GS} =0V, F=1.0MHz	-	316	-	PF
Reverse Transfer Capacitance	C _{rss}		-	14.5	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	10	-	nS
Turn-on Rise Time	tr	V_{DD} =50V,I _D =40A	-	6	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{G} =3 Ω	-	51	-	nS
Turn-Off Fall Time	t _f		-	9	-	nS
Total Gate Charge	Qg	V _{DS} =50V,I _D =40A,	-	76	-	nC
Gate-Source Charge	Q _{gs}	V _{DS} =50V,1 _D =40A, V _{GS} =10V	-	15.3		nC
Gate-Drain Charge	Q _{gd}	V _{GS} -10V	-	17.3		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =40A	-		1.2	V
Diode Forward Current (Note 2)	I _S		-	-	80	Α
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F =40	-	55	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	135	-	nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, $t \le 10$ sec.

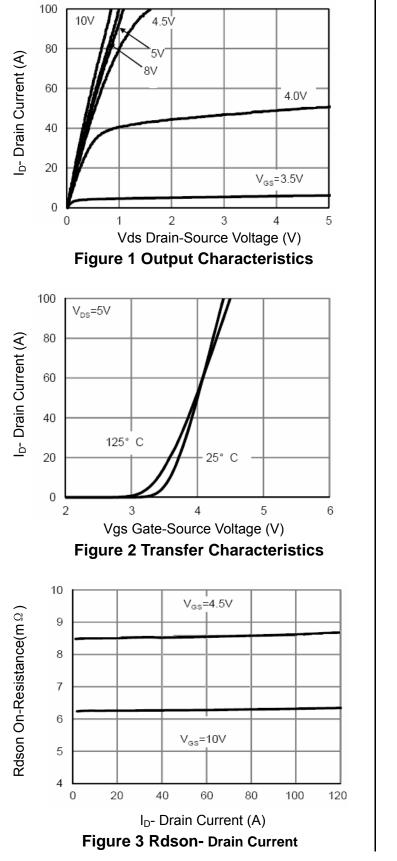
3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

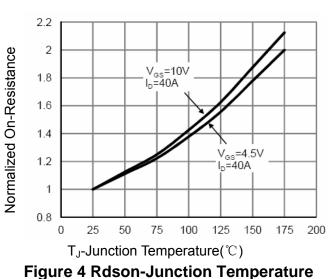
4. Guaranteed by design, not subject to production

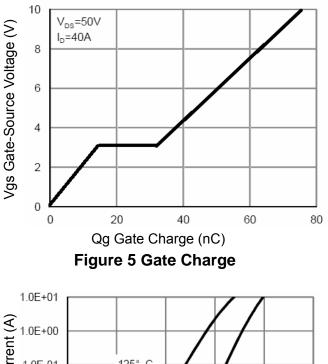
5. EAS condition : Tj=25 $^\circ C$,V_DD=50V,V_G=10V,L=0.5mH,Rg=25 Ω











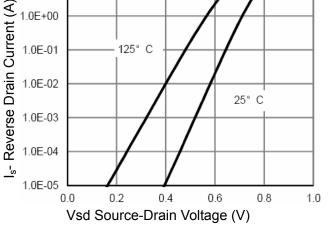


Figure 6 Source- Drain Diode Forward



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NCEP068N10AK

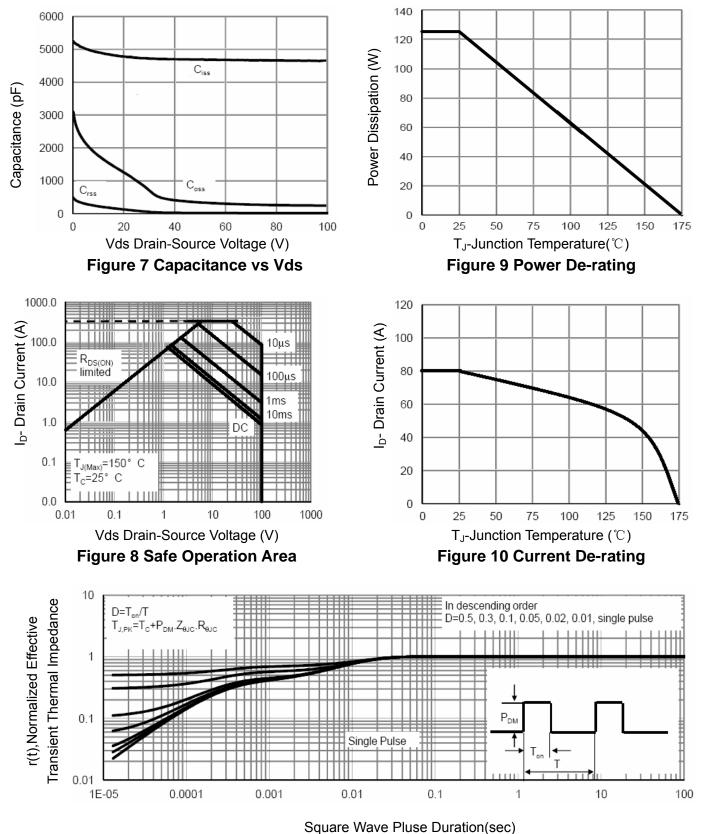
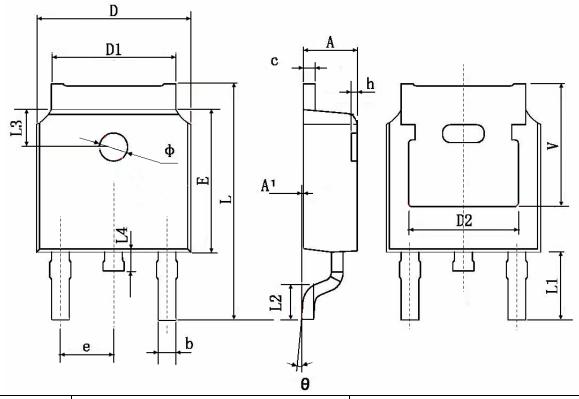


Figure 11 Normalized Maximum Transient Thermal Impedance



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TO-252-2L Package Information



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
	Min.	Max.	Min.	Max.	
А	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	4.83	TYP.	0.190 TYP.		
E	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.800	10.400	0.386	0.409	
L1	2.900	TYP.	0.114 TYP.		
L2	1.400	1.700	0.055	0.067	
L3	1.600	1.600 TYP.		TYP.	
L4	0.600	1.000	0.024	0.039	
Φ	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.350	TYP.	0.211 TYP.		



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